

Appl. No. 09/739,752; Group Art Unit: 2811
 Dkt. No. 1875.0220000; Batch No.:
 Inventor(s): Chen *et al.*; Tel: 202/371-2600
 Title: System and Method for One-Time Programmed Memory
 Through Direct-Tunneling Oxide Breakdown

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| APPROVED | O.G. FIG. | |
| BY | CLASS | SUBCLASS |
| DRAFTSMAN | | |

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FIG. 1

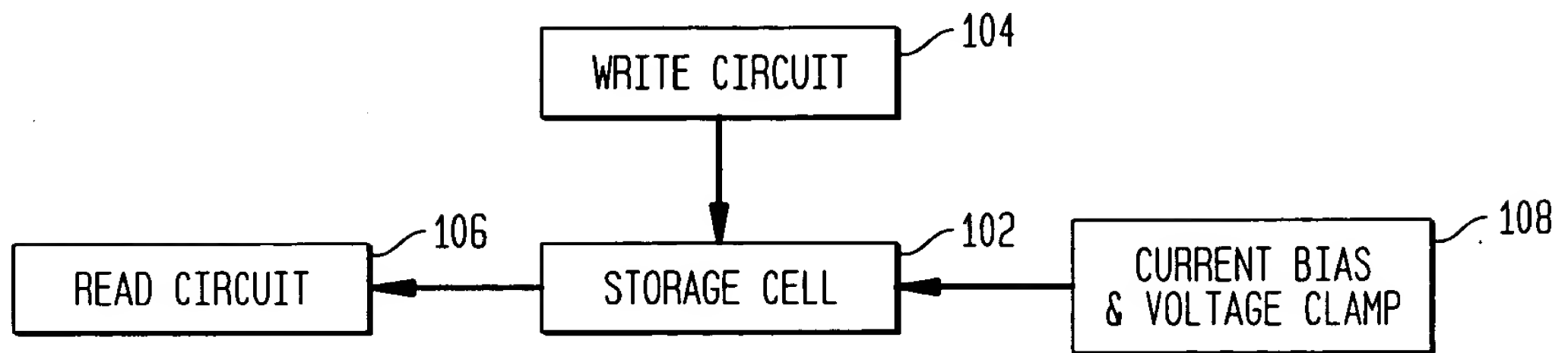
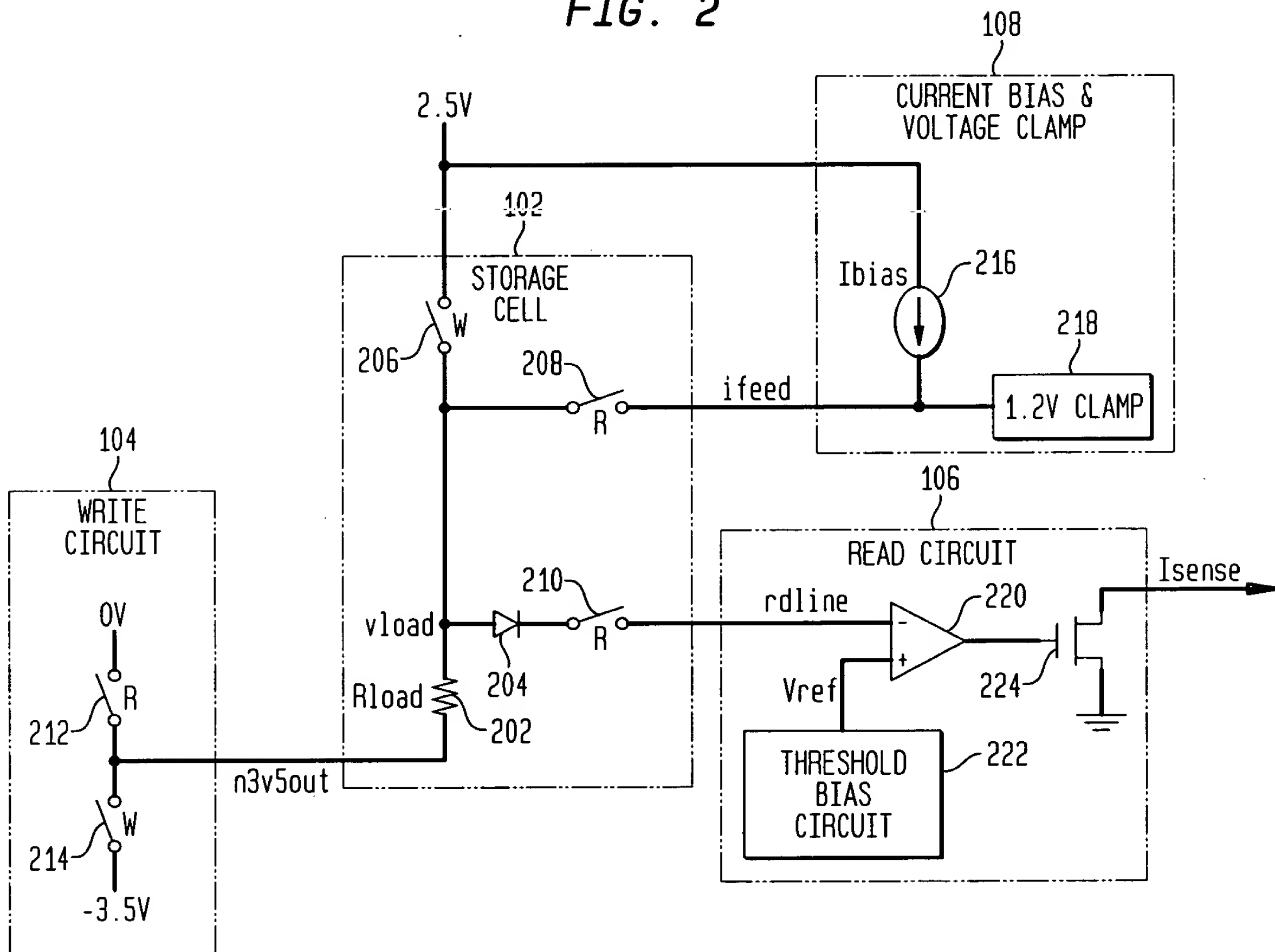


FIG. 2



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FIG. 3

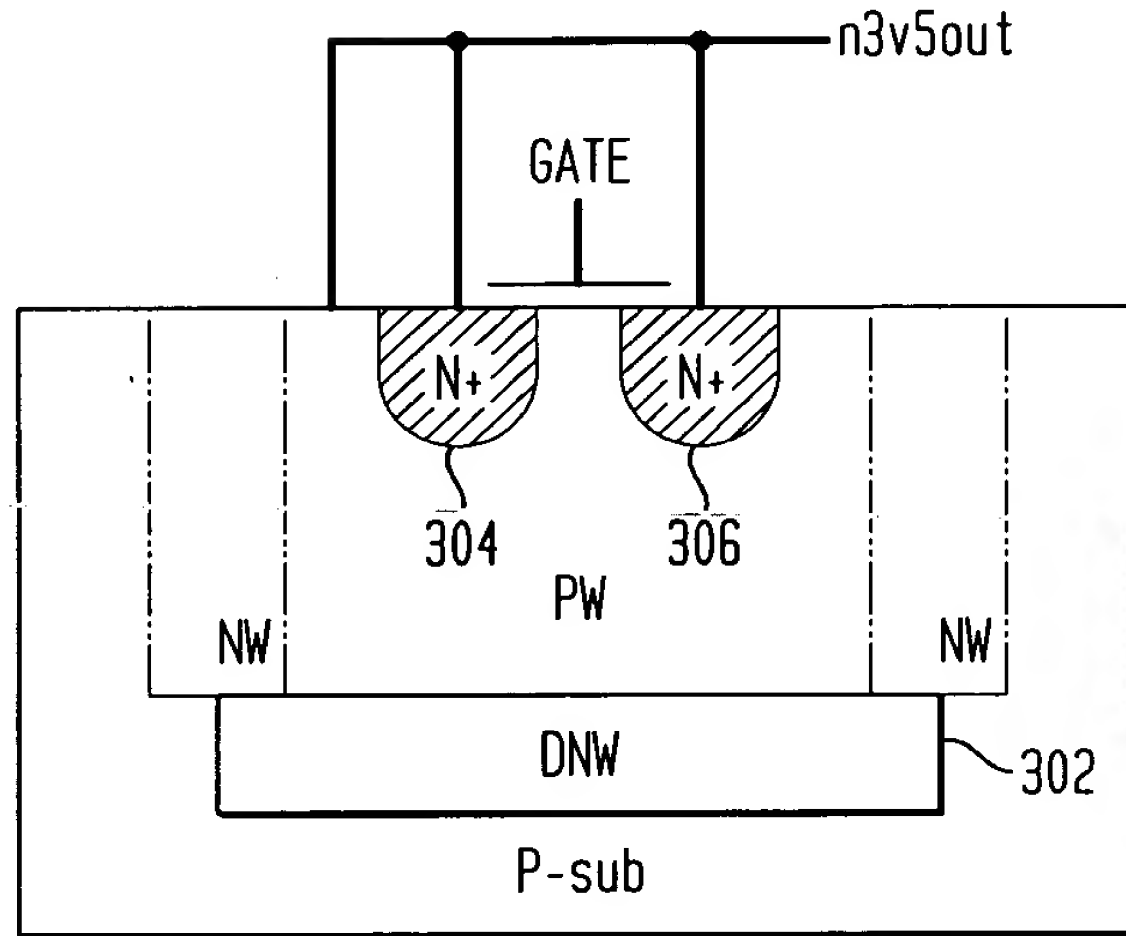
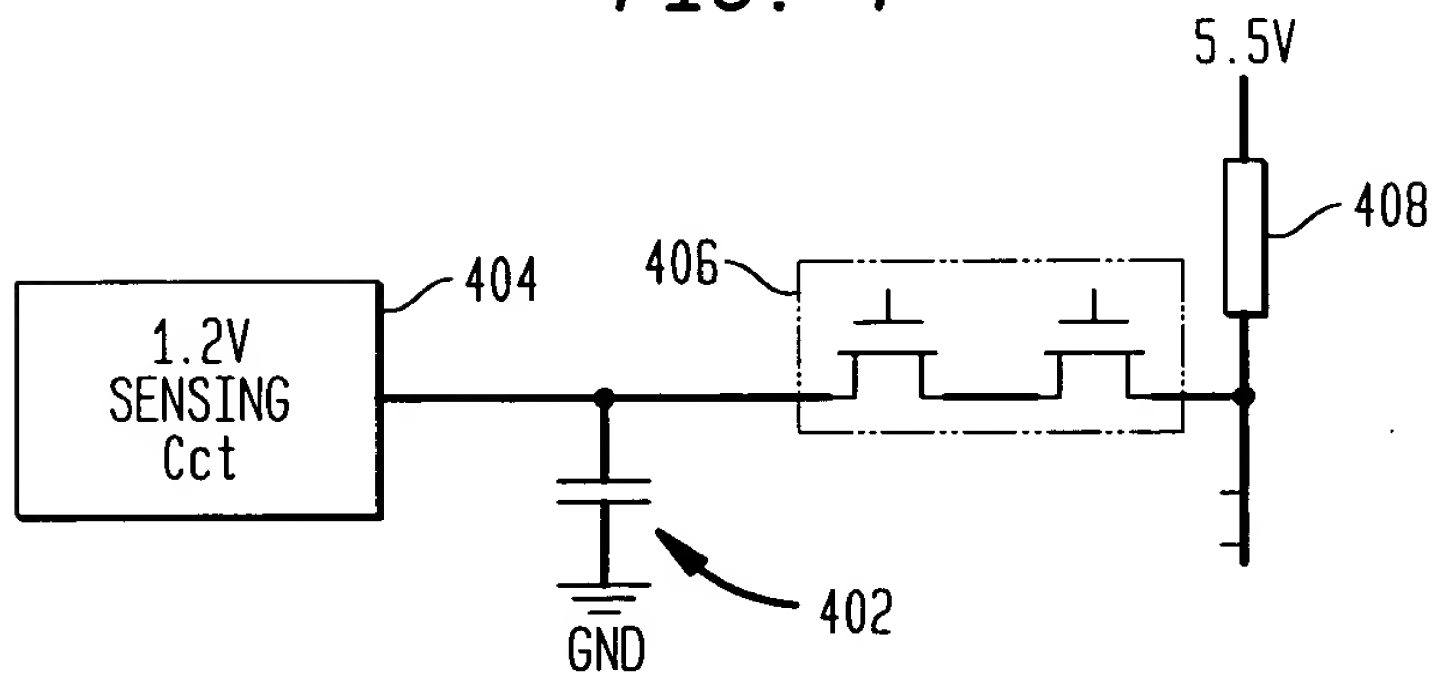


FIG. 4



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FIG. 5A

NMOS FET $10 \times 10 \text{ } \mu\text{m}^2$ S/D FLOAT

GATE CURRENT (A)

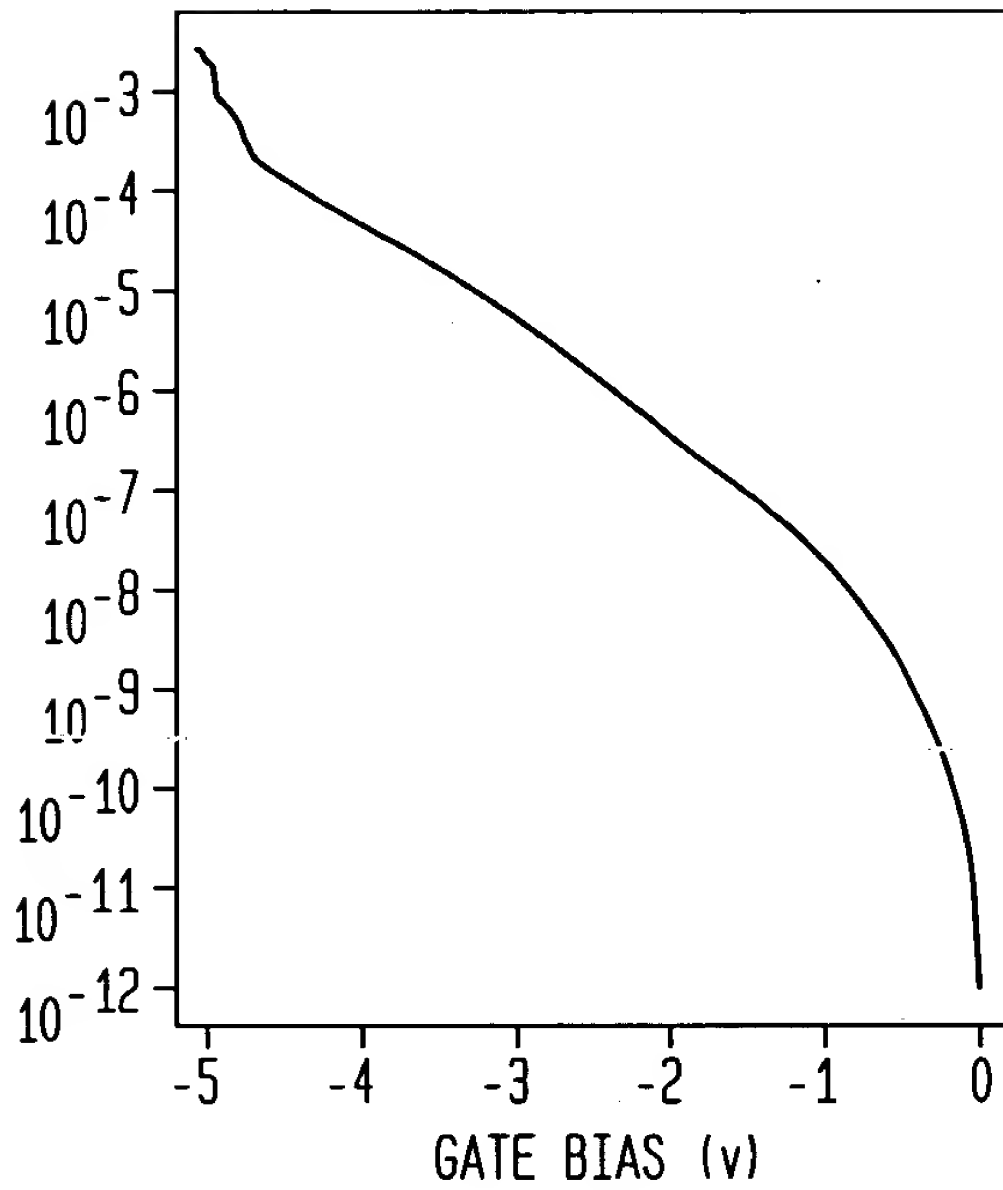
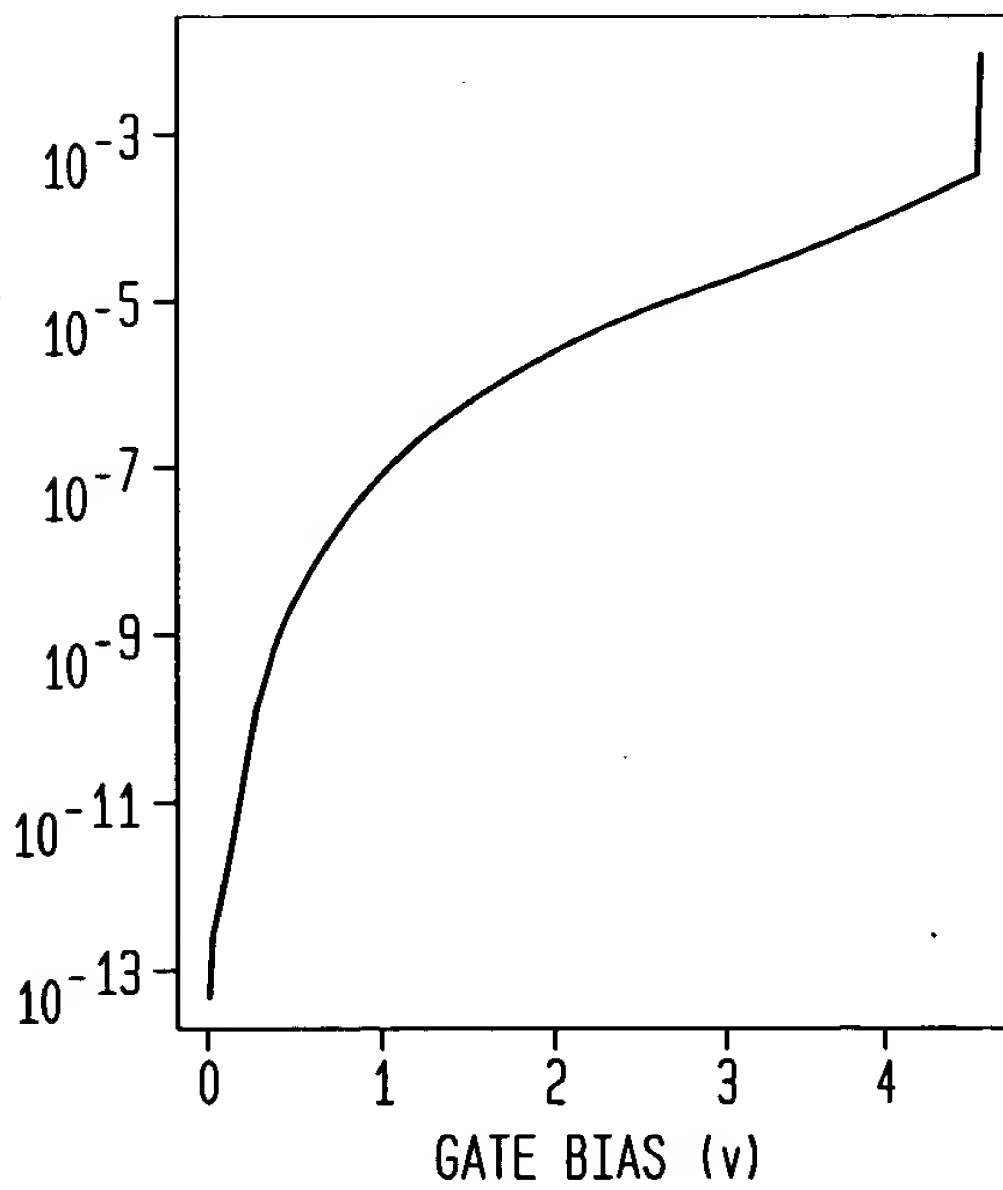


FIG. 5B

NMOS FET $10 \times 10 \text{ } \mu\text{m}^2$

GATE CURRENT (A)

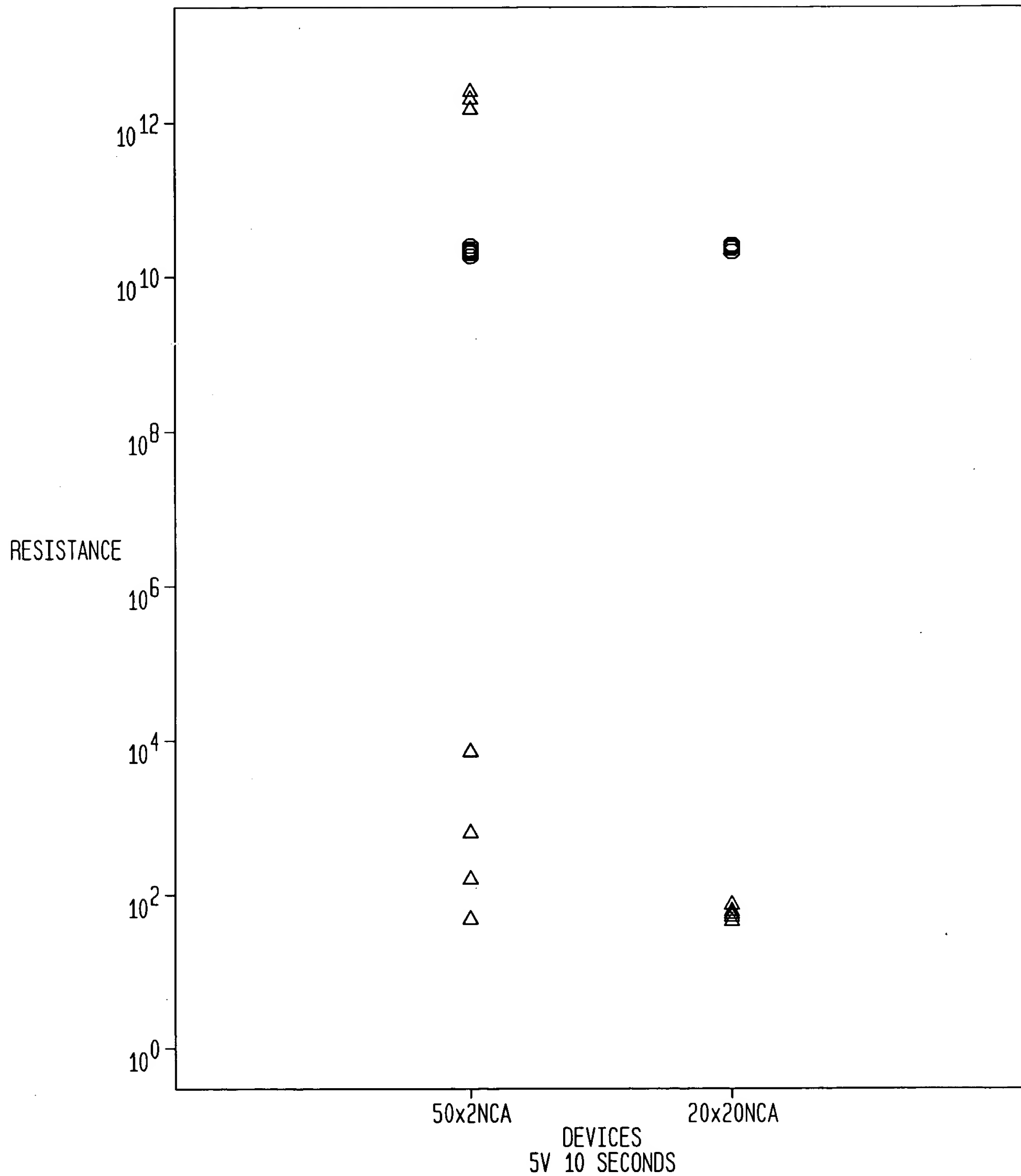


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FIG. 6A
 GATE OXIDE FUSE



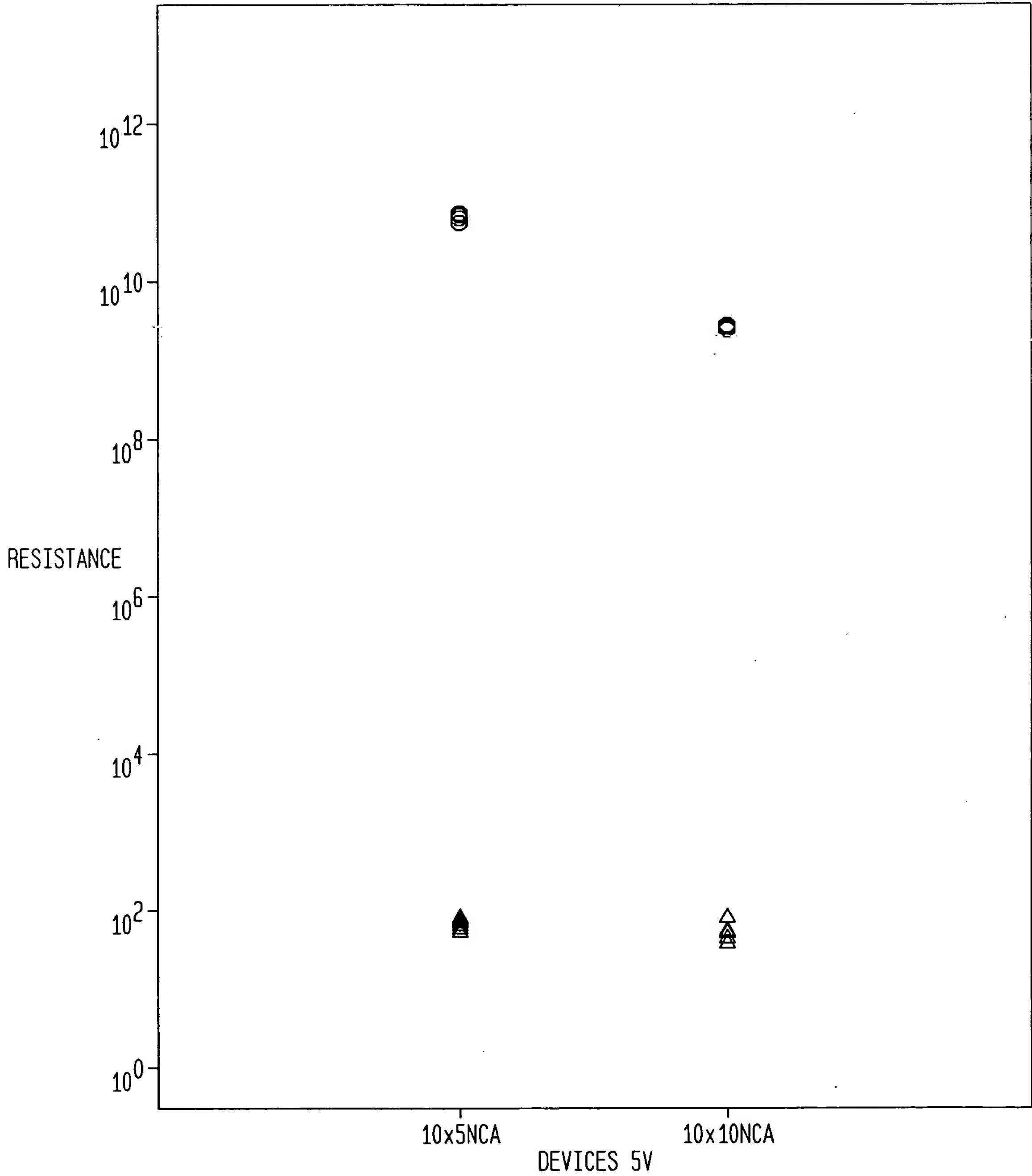
○ BEFORE (@vg=0.1)
 △ AFTER (@vg=0.1)

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| APPROVED | O.G. FIG. | |
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FIG. 6B
 GATE OXIDE FUSE



○ BEFORE (@vg=0.1)
 △ AFTER (@vg=0.1)

| | | |
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FIG. 7

